

MEMRISTOR-BASED ANALOG NEUROMORPHIC COMPUTING ENGINE DESIGN AND ROBUST TRAINING SCHEME

by

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University of Pittsburgh, 2014

The invention of neuromorphic computing architecture is inspired by the working mechanism of human-brain. Memristor technology revitalized neuromorphic computing system design by efficiently executing the analog Matrix-Vector multiplication on the memristor-based crossbar (MBC) structure. In this work, we propose a memristor crossbar-based embedded platform for neuromorphic computing system. A variety of neural network algorithms with threshold activation function can be easily implemented on our platform. However, programming the MBC to the target state can be very challenging due to the difficulty to real-time monitor the memristor state during the training. In this thesis, we quantitatively analyzed the sensitivity of the MBC programming to the process variations and input signal noise. We then proposed a noise-eliminating training method on top of a new crossbar structure to minimize the noise accumulation during the MBC training and improve the trained system performance, i.e., the pattern recall rate. A digital-assisted initialization step for MBC training is also introduced to reduce the training failure rate as well as the training time. We also proposed a memristor-based bidirectional transmission exhibition/inhibition synapse and implemented neuromorphic computing demonstration with our proposed synapse. Experiment results show that the proposed design has high tolerance on process variation and input noise. Different benefits of MBC system and new synapse-based system will be compared in our thesis.

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PREFACE

Over the past three years of studying at University of Pittsburgh, I have learned a tremendous amount. Here, I want to thank my supervisor, Professor Yiran Chen, for all his support and guidance during my Master Program. Also, I am very thankful to Dr. Hai Li, Dr. Mingui Sun and Dr. Zhi-hong Mao for their kindly consenting to be my committee members. I appreciate all of the extremely helpful suggestion discussion. I thank all the lab members in Dr. Chen's research group as well as all my friends here in University of Pittsburgh.

1.0 INTRODUCTION

The explosive growth of the functional variety of modern embedded systems leads to the emergence of Multiprocessor System-on-Chip (MPSoC) [7]. However, the functionalities of various processing elements on a MPSoC are usually determined at system architect and design stages. Any changes beyond the system capability may incur architecture change, circuit redesign or even new chip fabrication with high cost. The application of programmable elements, such as GPU, mitigates the redesign cost, but achieving the system reconfigurability and power efficiency simultaneously still remains as a challenge [11].

The emerging of neuromorphic computing system successfully addresses this challenge by providing functionality reconfiguration as well as low power consumption, especially for the computational intensive applications. Although many neuromorphic computing algorithms have been proposed for many applications like signal processing, pattern recognition, surveillance etc. limited progress was made on the VLSI realization of neuromorphic computing systems [1]. Based on the prediction of Prof. Leon Chua in 1972 [2]. HP Labs discovered a memristor device. A memristor can record the historical profile of the electrical excitations applied on it and incur corresponding resistance change [12]. The similarity between this memristive effect and biologic synaptic have motivated many breakthroughs in the design of the neuromorphic hardware systems [4, 5]. A lot of memristor based synapse designs have been proposed for cognitive computing tasks. For higher connection density and efficiency memristor-based crossbar (MBC) structure is

recently introduced to improve the execution of the Matrix-Vector multiplications, which is one of the most common operations in the mathematic representation of artificial neural network (ANN) [6, 3]. However, there are three major technical challenges in such designs: 1) Due to the difficulty of real-time monitoring the memristor state, the off-line training, e.g., directly programming the resistance of a single memristor to the target value is unlikely possible [4]; 2) The input vector-based iterative training methods, however, usually suffer from the long convergence time [3]; and 3) The input signal noise and process variations severely affect the training efficiency and reliability.

In this work, we quantitatively analyzed the sensitivity of the MBC programming to the process variations and input signal noise. We then proposed a noise-eliminating training method with the corresponding modified crossbar structure to minimize the noise accumulation during the MBC training and enhance the trained system performance, i.e., the pattern recognition rate. A digital-assisted initialization step for MBC training is also introduced to reduce the training failure rate as well as the training time. Experimental results show that our technique can significantly improve the performance and training time of neuromorphic computing system by up to 39.35% and 23.33%, respectively.

At the same time, we also conduct research on more flexible memristor-based synapse design that will give us better efficiency on certain cognitive computing tasks. The design is inspired by bidirectional biological synapse structure. The memristor is used as gate voltage controller to dynamically control the current going through the transistor, which represent “synaptic” behavior.

2.0 BACKGROUND

2.1 MEMRISTOR BASICS

Figure 1(a) depicts an ion migration filament model of HfO_x memristors [9]. A HfO_x layer is sandwiched between two metal electrodes TE (top electrode) and BE (bottom electrode).

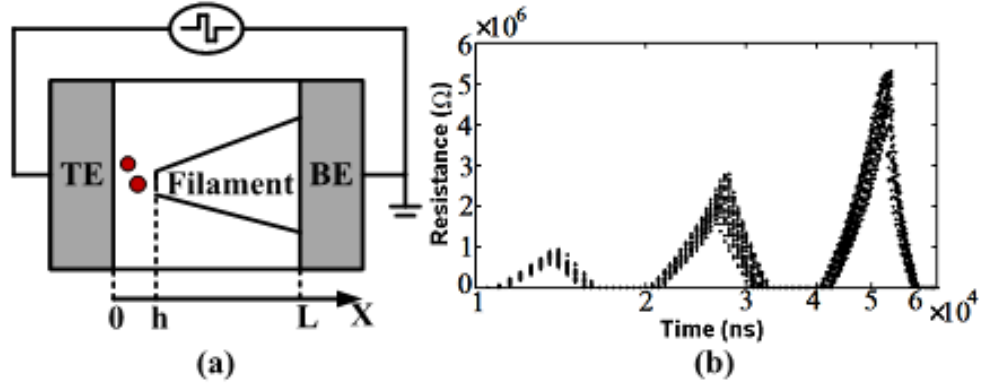


Figure 1. (a) Metal-oxide memristor [10]. (b) Resistance distributions of MLC memristor.

During the reset process, the memristor switches from low resistance state (LRS) to high resistance state (HRS). The oxygen ions migrate from the electrode/oxide interface and recombine with the oxygen vacancies. A partially ruptured conductive filament region with a high resistance per unit length R_{off} is formed on the left of the conductive filament region with a low resistance per unit length R_{on} as shown in Figure 1(a). During the set process, the memristor switches HRS to LRS. The ruptured conductive filament region shrinks. We define L as the total thickness of the

oxide layer and h as the length of the ruptured conductive filament region, respectively. The resistance of the memristor R can be calculated by [9][15]:

$$R = R_{off} h + R_{on}(L-h). \quad (1)$$

We note that the memristor resistance can be programmed to any arbitrary value by applying a programming current with different pulse width or magnitude. Note that the memristor resistance changes only when the applied voltage is above a threshold, e.g., V_{wrth} .

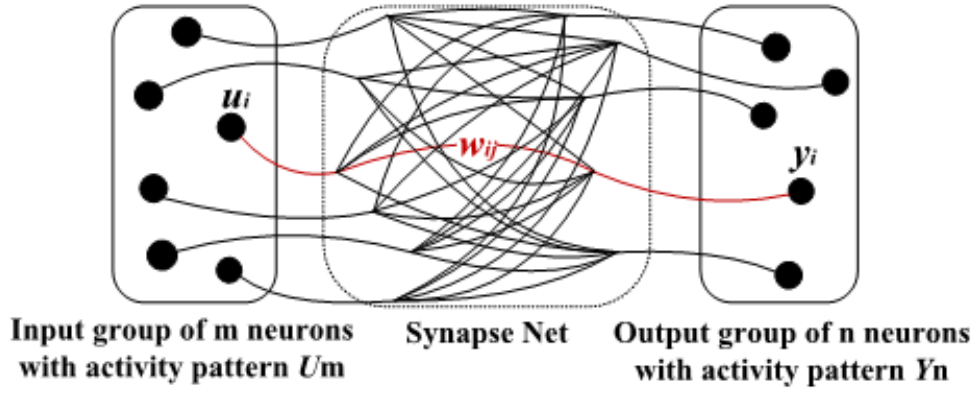


Figure 2. Conceptual overview of neural network [3].

2.2 MBC-BASED COMPUTING

Fig. 2 depicts a conceptual overview of a neural network. Two groups of neurons are connected by a set of synapses. The output neurons collect the information from the input neurons through the synapses and process them with certain activation function. The synapses apply different weights (synaptic strengths) on the information during the transmission. In general, the relationship between the activity patterns of the input neurons \mathbf{U} and the output neurons \mathbf{Y} can be respectively illustrated as:

$$\mathbf{Y}_n = \mathbf{W}_{n \times m} \times \mathbf{U}_m. \quad (2)$$

Here the weight matrix $W_{n \times m}$ denotes the synaptic strengths between the two neuron groups. In neuromorphic computing system, the Matrix-Vector multiplication represented in Eq. (2) is one of the most frequent operations [10][14]. Because of the structural similarity, reconfigurable resistive array, e.g., MBC is conceptually efficient to execute the Matrix-Vector multiplications [3]. During the operation of MBC-based computing, \mathbf{U} is mimicked by the input voltage vector applied on the word-line (WL) of the MBC. Every memristor in the MBC is programmed to the resistance state representing the weight of the corresponding synapse [17]. The current along every bit-line (BL) of the MBC is collected and converted to the output voltage vector \mathbf{Y} by the comparator circuit. Please refer to the appendix for more details on the operation of the MBC-based neuromorphic computing engine.

2.3 TRAINING METHOD OF MBC

The training of MBC is defined as the process of programming the resistances of the memristors in the MBC to the value representing the connection matrix in Eq. (2). Training method is also derived from the close-loop training algorithm of the weight matrix in ANN theory, e.g., gradient descent training [8]. During the training process, the weight matrix \mathbf{W} is updated iteratively until the difference between the output y and the target output y^* reaches the minimum. In each iteration, \mathbf{W} is adjusted based on the gradient of the output error $|y - y^*|$ as:

$$\Delta w_{ij} = \mu \cdot \left(\frac{\partial (y - y^*)^2}{\partial w_{ij}} \right). \quad (3)$$

Here w_{ij} is the element in the \mathbf{W} connecting the neuron i and j , or the resistance of the memristor at row i and column j in the MBC. Δw_{ij} is the change of w_{ij} during the iterations. μ is the training rate. The choice of μ is discussed in [3].

3.0 NOISE-ELIMINATING TRAINING

3.1 IMPACTS OF DEVICE VARIATION AND NOISE

Process variation and signal noise are two major factors affecting the robustness of MBC-based computing and training processes. Figure 3(a) shows an example of the output comparison step in the MBC training process when a set of read voltage V_{rd} , 0, $V_{rd}/2$ is applied to the WLs of three memristors R1 -- R3 in the same column. Here we assume the three memristors are all at HRS. The ideal voltage on the BL shared by these three memristors should be $V_{rd}/2$. However, the device non-uniformity and the input voltage fluctuation may cause the bias changes on the memristors. For example, if the resistance of R1 is larger than that of R2, the voltage on the BL will be below $V_{rd}/2$, as shown in Figure 3(a). Also, if the input voltages on the WL of R1 changes to $V_{rd} + \Delta V$, the voltage on the BL will be above $V_{rd}/2$, as shown in Figure 3(b). In both cases, the calculated difference between the current output and the target output will be different from the ideal case. Such deviation can be accumulated along with the training iterations. Together with the fluctuations of the programming voltage and the process variations, it will cause the deviation of the programmed memristor resistance from the ideal value during the programming step in the MBC training process and finally affect the computation accuracy. We use an example to illustrate the impacts of the process variation and input signal noise on the MBC training. A 64 x 64 MBC is implemented to realize the synapse connection of a two-layer neural network.

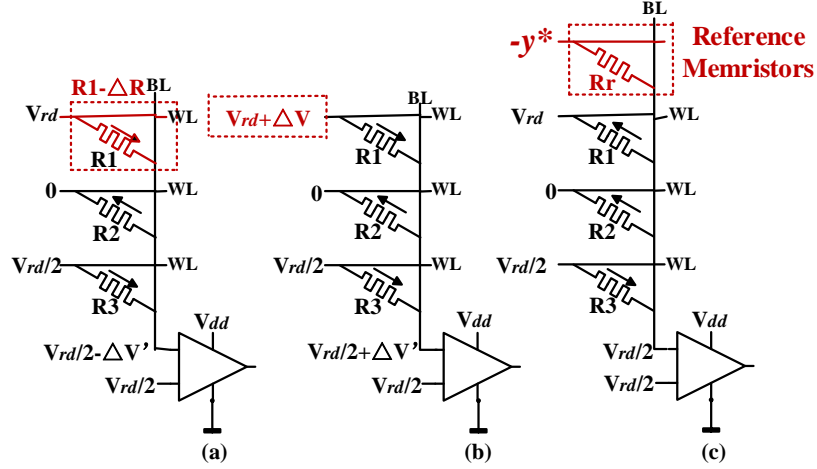


Figure 3. Training with (a) memristor variation. (b) voltage noise. (c) reference memristors.

Figure 4 shows the resistance difference between the ideally trained MBC (no process variation or input signal) and the MBCs trained with considering process variation (top row) or input signal noise (bottom row), respectively. In the evaluation of process variation's impact, the distribution of the memristor cell size in the MBC is generated randomly for every iteration with Gaussian distribution. Note that since the input noise for write will result in the variation of the MBC memristance, we consider the write input noise with process variation together. The standard deviation of the memristance variation is assumed to be 10% ($\sigma = 0.1$), 20% ($\sigma = 0.2$), and 30% ($\sigma = 0.3$) of its nominal value. In the evaluation of the read input signal noise's impact, similarly, a random noise following Gaussian distribution is generated on the input signals of the MBC in every iteration. The standard deviation of the noise is assumed to be 10% ($\sigma = 0.05$), 20% ($\sigma = 0.1$), and 30% ($\sigma = 0.15$) of V_{rd} . The mean of the noise is zero. Gradient descent rule is applied in the training.

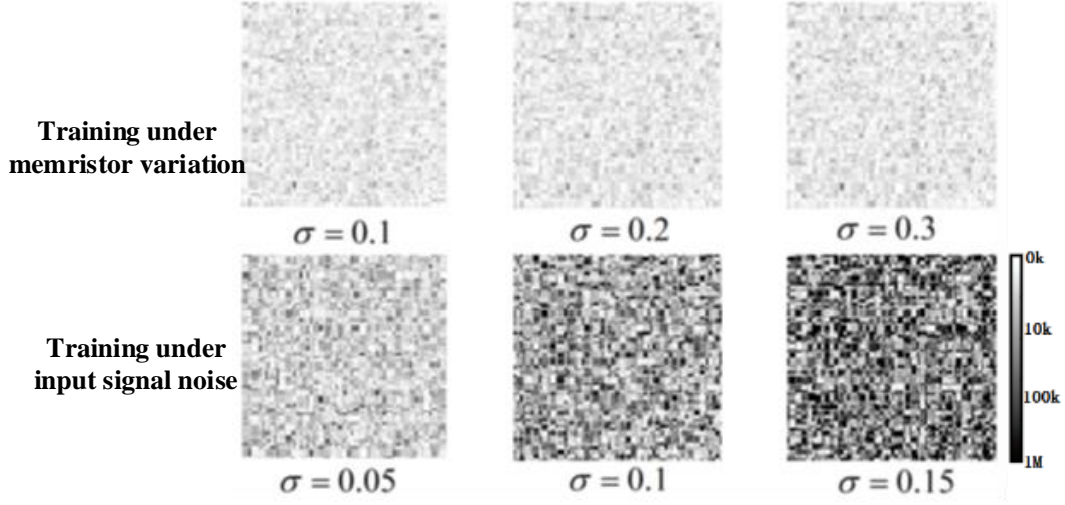


Figure 4. Training quality with ideal memristor and memristor with different variations.

Our simulation shows very marginal degradation in the training robustness as the process variation increases. It is because the device variations are reflected in the difference between the current output and the target output during each iteration and compensated by close-loop training. Similarly, write pulse noise will cause memristance change variation in each iteration, which will also be compensated by close-loop training. However, input signal noise is generated on-the-fly and accumulated during the training process, leading to a large difference from the ideal trained result.

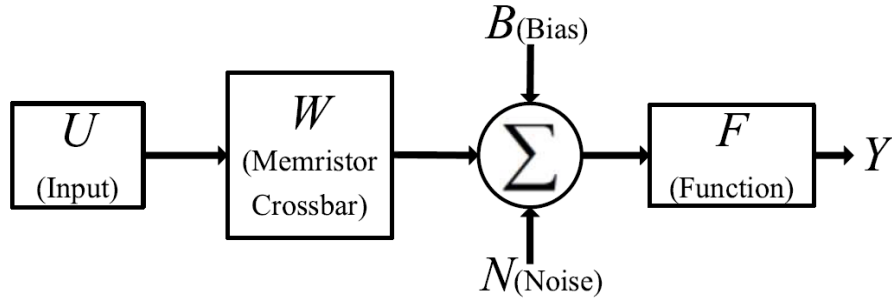


Figure 5. Training process with noise.

3.2 NOISE SENSITIVITY OF MBC TRAINING

Figure 5 illustrates how the process variations and input signal noise affect the MBC training. Now, let us explain how this dynamic threshold training scheme works in system level (shown in Figure 4). We assume F is the output function of the MBC, *i.e.*, comparators, which translates the output of the MBC to a digital value $\in \{1, -1\}$. The input signal noise N is added on the F before it is sent to the next iteration. Different from the conventional gradient descent training, our method tries to minimize not only the 2-norm output distance $(y - y^*)^2$, but also the system's sensitivity to the noise $\frac{\partial f(\sum u_i w_{ij})}{\partial N}$ as:

$$\underset{w}{Min}: J = \overbrace{(y - y^*)^2}^{J_1} + \overbrace{\frac{\partial f(\sum u_i w_{ij} + \text{nosie})}{\partial N}}^{J_2}. \quad (4)$$

3.3 NOISE-ELIMINATING TRAINING SCHEME

Based on our observation on Eq.(4), we proposed a noise-eliminating training scheme to minimize the noise accumulation during the MBC training. Redundant rows are added on top of the memristor array to generate an offset current B that is opposite to the target output of the column

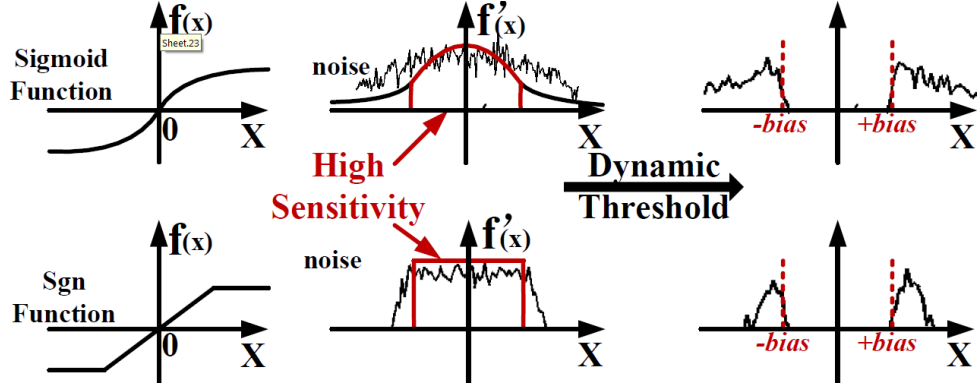


Figure 6. Noise elimination mechanism.

y_i^* during MBC training, as shown in Figure 3(c). It adds the bias bias to the calculated difference between the current output and the target output of the MBC so that the $|\sum u_i w_{ij}|$ is shifted out of the sensitive region of the activation function $f(x)$ as:

$$x = \begin{cases} \sum w_{ij} w_{ij} u_i < \text{bias } y^* & \text{if } y^* = +1 \\ \sum w_{ij} u_i > \text{bias } y^* & \text{if } y^* = -1 \end{cases} \quad (5)$$

As shown in Figure 6, through applying bias, the residue of the noise in the sensitive region of the activation function is reduced and the accumulation of the noise during the training iterations is minimized. The selection of bias is important in our proposed scheme: A bias larger than necessary may make the training process bypass the convergence region, leading to the difficulty of convergence. If bias is too small, it may not efficiently suppress the noise. A detailed evaluation on the selection of bias will be given in Section 5.

We define bias *amplitude* a to measure the ability of the reference memristor to offset the MBC output as:

$$a = \frac{R_{on} N_{ref}}{R_{ref} N_{col}} \quad (6)$$

Here R_{on} is the HRS of a memristor. R_{ref} is the average resistance of the reference memristors. N_{col} is number of memristors in a column. N_{ref} is the number of reference memristors in a column. During the MBC training, a training failure is defined as the unsuccessful convergence after the maximum n iterations of training. Here n is the threshold usually much more than the normal iteration number required for convergence. If a training failure happens, we will reset the reference memristors to reduce a and redo the training process until the training succeeds or $a=0$, which indicates the training is degraded to conventional training scheme.

4.0 DIGITAL-ASSISTED INITIALIZATION

4.1 BASIC IDEA

In our noise-eliminating training scheme, the introduction of bias affects the convergence process of MBC training and may cause the potential convergence failure. In this section, we proposed a digital-assisted initialization step to the MBC training to reduce the training failure rate and training time.

As shown in Figure 7, in the initialization step, the target W , which is normally known in the algorithm, is quantized to its digital version W_D where every element is represented by a MLC data, e.g., 2-bit digit. W_D is then written into the MBC by the open-loop training method, regardless the device variations. Our digital-assisted training initialization step can improve the convergence speed of MBC training by setting the initial resistance of the memristors close to the target value. The robustness of the training process is also improved as the possibility of being stuck in the local minimum reduces accordingly. Different from the open-loop training, the digital initialization does not require to program the memristor to the digitalized resistance level precisely and can tolerate the device variations. Note that the digitalization of W relies on specific training algorithms as we will show next for our approach.

4.2 DIGITALIZATION OF WEIGHT MATRIX

In the conventional MLC memory cell design, the distances between the two adjacent resistance states of the memristor must be the same to maximize the sense margin [5]. The threshold to differentiate the different MLC level is set to the cross point between the distributions of two adjacent resistance states. In MBC training, the convergence rate of the training process is conceptually determined by the distance between the target value and the initial value. Therefore, the partition method of MLC memory design does not necessarily give us the minimum distance in the digitalization of weight matrix W .

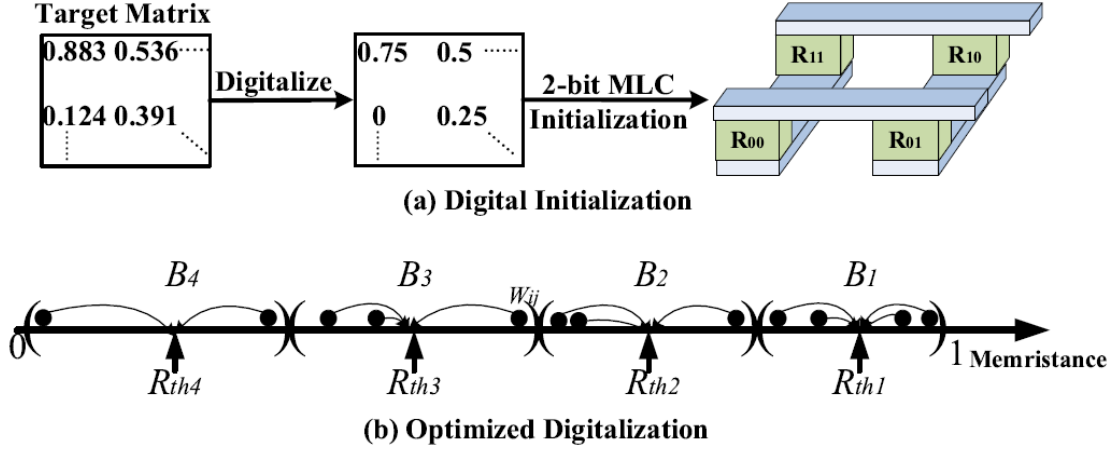


Figure 7. Digital-assisted Initialization.

We propose a heuristic method to determine the resistance states of the memristor corresponding to the different digitalized levels of W : For an M -level digitalization, the elements of W are equally classified into M baskets B_i , $i=1 \dots M$ based on their values. We then find the R_{thi} , $i=1 \dots M$ for each basket to achieve the minimum $\sum |W_{ij} - R_{thi}|_{W_{ij} \in B_i}$, $i = 1 \dots M$, R_{thi} the optimal

memristor resistance states for the i level of the digitalization. Here we used 1-norm resistance distance to measure the impact of the difference between W_{ij} and $W_{D,ij}$ on the overall convergence rate of the MBC training. For different MBC training algorithms, other methods, e.g., based on 2-norm distance or the maximum distance, may be also adopted. Considering the practical memristor programming resolution, we set $M=4$ here. Note that this method may cause smaller MLC sensing margin, however, we do not need to read out the value of each MLC. The initialization accuracy is enough to guarantee the training quality.

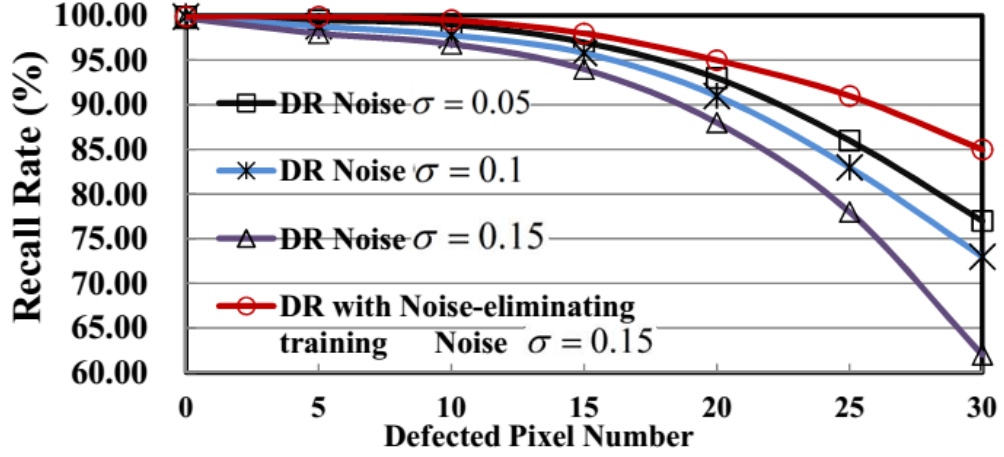
5.0 TRAINING QUALITY EVALUATION

5.1 NOISE ELIMINATION

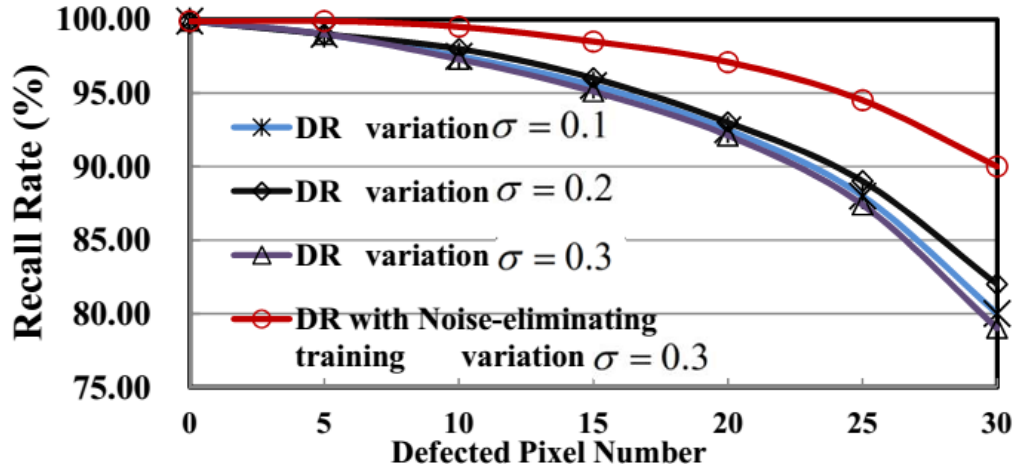
Figure 8 illustrates the effectiveness of the noise-eliminating training method on improving the performance of MBC-based computing engine. A Hopfield Network with 128 input neurons is built on a 128×128 MBC with one-layer iterative structure to remember 16 patterns. We choose conventional DR training method for comparison. In our simulation, we set the *bias amplitude* a to 0.05. Monte-Carlo simulations are conducted under different process variations and input signal noise levels to measure the success rate when recognizing the image. As shown in Figure 8 (a) and (b), even at the worst case of $\sigma_{\text{variation}}=0.3$ or $\sigma_{\text{variation}}=0.15$ at each comparison, our method still achieves the best performance.

Table 1, Experiment Setup

MBC	Single MBC Size	Input Voltage Noise		Memristor Variation
	512×512	$\sigma = 0.1$		$\sigma = 0.1$
Neuromorphic Engine	Neuron Number in Input Layer	Neuron Number in Hidden Layer		Neuron Number in Output Layer
	16384 (32×MBC)	16384 (32×MBC)		3
Peripheral Circuit	G	Vref (V)	Vdd/Gnd (V)	Vrd(V)
	50	0.6	1.2/0	0.1
	Amplifier Comparator			Registers
	Programming pulse voltage(V)	Programming pulse width(ns)	Number of Comparators/MBC	Number of Registers/MBC
	2.5/-2.5	50	512	512



(a)



(b)

Figure 8. Noise-eliminating training (a) with signal noise; (b) with memristor variation

5.2 DIGITAL-ASSISTED INITIALIZATION

Figure 9 compares the training speed of the same MBC design simulated in Section 5.1. Y-axis is the Hamming distance between the output vectors of the MBC and the target output vectors. X-axis is training iteration number. The size of training input vector set is 16 and the MBC

training ends when generated output matches the target patterns. Four combinations of process variations and input signal noise levels are simulated. To exclusively measure the effects of digital-assisted initialization, noise-eliminating training is not applied in the simulations.

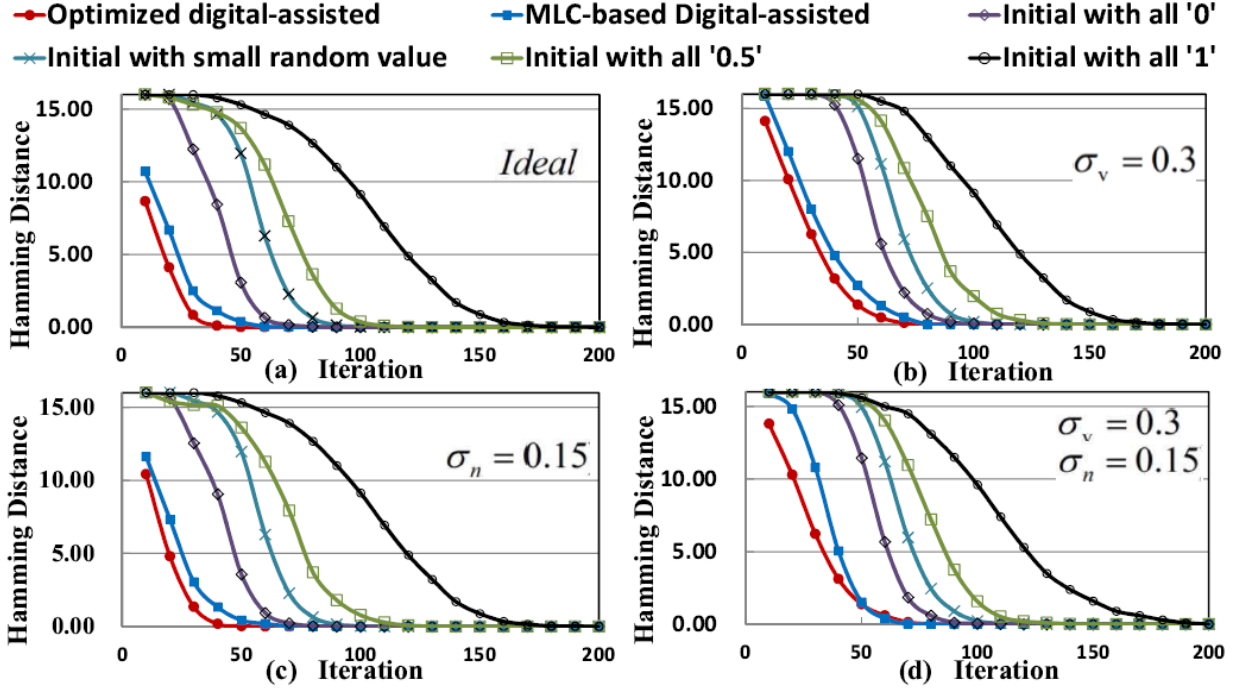


Figure 9. Train speed. (a) Ideal case. (b) $\delta_v = 0.3$. (c) $\delta_v = 0.15$. (d) variation and noise.

“MLC-based digital-assisted” curve denotes the results of using the digitalization method of 2-bit MLC memory design in W initialization while “Optimized digital-assisted” curve denotes the results of using the heuristic method proposed in Section 4.2. Both of them demonstrated much lower iteration number than the other training process without the digital-assisted initialization step. Our heuristic method offers the best result among all the training methods: when both process variation and input signal noise are considered, the training iteration number of “Optimized digital-assisted” is 23.3% less than that of “initialization with '0'”.

The introduction of process variation causes the deviation of the initial states of the memristors from the target states in the digital-assisted initialization step. It raises the Hamming distances of the first several iterations and increases the iteration numbers considerably, as shown in Figure 9(b) and (d).

In general, the total training time of a conventional BP training method can be calculated by:

$$T_t = (T_p \cdot n^2 + T_c \cdot n) \cdot N_{iter}. \quad (7)$$

Here n is the input size of the MBC. T_t is overall training time. T_p and T_c are the programming and comparison time consumed in each iteration. N_{iter} is the number of iterations. When the digital-assisted initialization step is applied, the initialization time T_{init} is added to the total training time. Therefore, to achieve the positive benefit, the speed up introduced by the digital-assisted initialization step must be larger than the extra initialization time. Figure 10 shows that for a MBC with the size of $n < 128$, digital-assisted initialization step does not give us any benefits on the training time reduction under the simulated conditions.

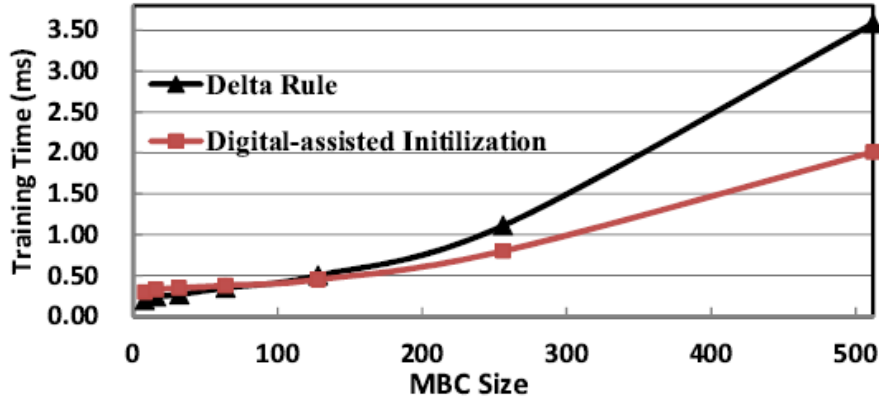


Figure 10. The impact of initialization on total training time.

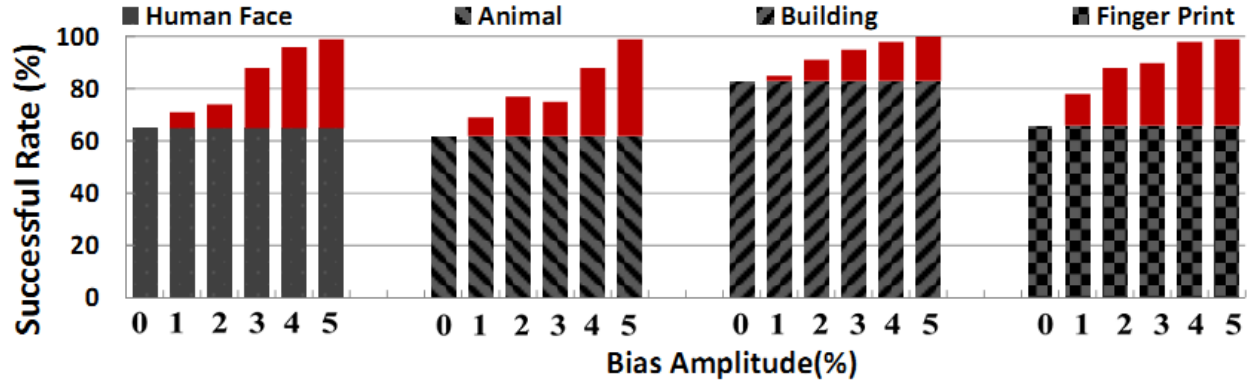
5.3 CASE STUDY

To comprehensively evaluate effectiveness of all our proposed techniques, we implemented a three-layer feed forward neural based on a neuromorphic computing system with multiple 512×512 MBC computing engines. BP training is used as comparison training algorithm in this case. Other simulation parameters can be found at Table 1.

Four sets of image patterns (*e.g.*, face, animal, building and finger print) are adopted in the training neuromorphic computing systems. As shown in Figure, each pattern set has 8 images with a size of 128×128 pixels.



(a)



(b)

Figure 11. 3-layer network recall rate. (a) Standard patterns; (b) Successful recognize rate.

Figure 11 compares the recall success rates of the conventional back propagation (BP) training and the modified noise-eliminating method. Our method surpasses the conventional training method over all the simulation cases. Following the increase in the bias amplitude, the

recall success rate improvement introduced by the noise-eliminating training method becomes more prominent.

Table 2, Training Failure Rate

Bias Amplitude " a "		0	0.01	0.02	0.03	0.04	0.05
Training Failure Rate " P_f " (%)	Human Face	0.61	1.9	4.2	7.3	15.4	31.5
	Animal	0.44	3.2	7.2	11.1	24.4	51.5
	Building	0.56	2.1	3.9	6.6	13.5	26.1
	Finger Print	0.39	2.7	4.5	9.1	19.4	41.7
Training Time " T_t " (ms)	Human Face	2.82	2.77	2.63	2.59	2.55	2.53
	Animal	2.76	2.57	2.56	2.40	2.28	2.25
	Building	2.66	2.5	2.48	2.34	2.31	2.28
	Finger Print	2.53	2.39	2.28	2.19	2.11	2.10

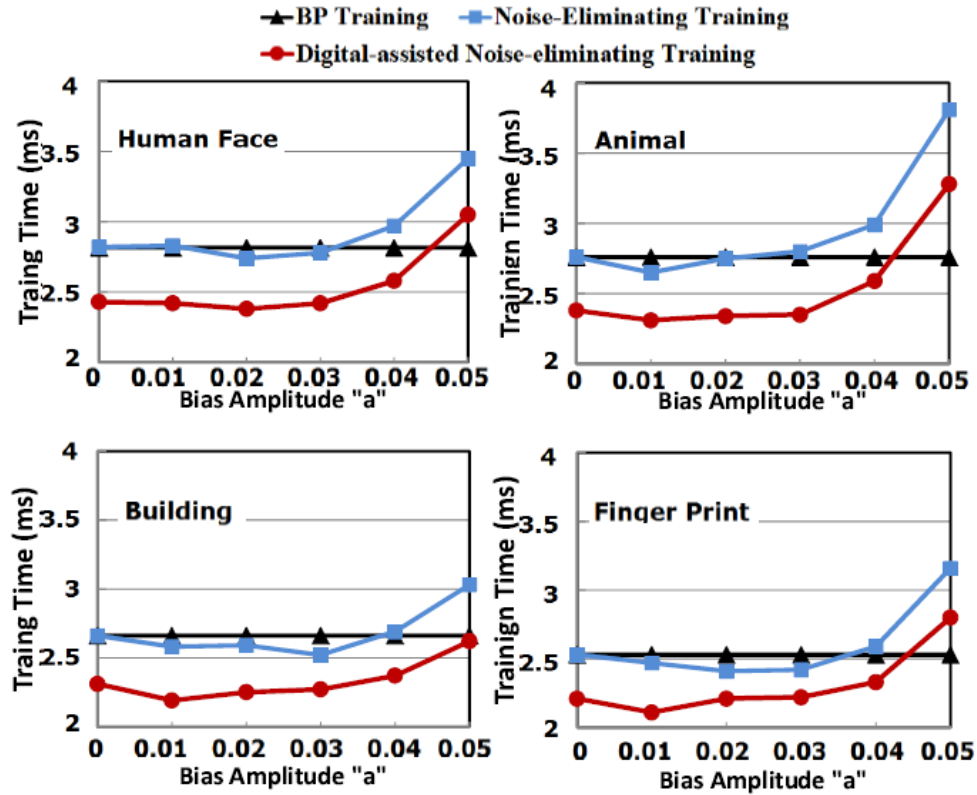


Figure 12. Comparisons of overall training time.

Table 2 shows the training failure rate and the training time (without digital-assisted initialization step) under the different bias amplitude. The increase in bias amplitude results in the reduction of the training time for each iteration while rapidly raises the training failure rate. As aforementioned in Section 3.3, Training failure will prolong the total training time since we will redo the training with a reduced a . The overall training time T_{train} will become:

$$T_{\text{train}} = T_{t(a=a_1)} + P_{f(a=a_1)} \cdot (T_{t(a=a_2)} + P_{f(a=a_2)} \cdot (T_{t(a=a_3)} + \dots) \quad (8)$$

where $T_{t(a=ai)}$ and $P_{f(a=ai)}$ are training time for each iteration and training failure rate for the training process with bias amplitude $a = ai$.

Figure shows the overall training time comparison between conventional back propagation (BP) training, the modified noise-eliminating training with and without the digital-assisted initialization step starting with different a . Our techniques generally reduce the MBC training time by 12.6~14.1% for the same recall success rate, or improve the recall success rate by 18.7%~36.2% for the same training time. Designer can pick the best combination based on the specific system requirement.

6.0 NEW MEMRISTOR-BASED SYNAPSE DESIGN

6.1 BIOLOGY INSPIRED SYNAPSE DESIGN

In real biology neural system, there are chemical synapses and electrical synapses working as connections between neurons. Electrical synapses have unique characteristic of bidirectional transmission, which is also very important for implementation of artificial neuromorphic computing system [20]. In order to implement bidirectional transmission, two sets of input/output are needed for one synapse, and the transmission direction should be controlled by a switch signal. Figure 13 shows the schematic of memristor-based bidirectional transmission synapse with two neurons it connects. The resistance R and memristance M determine the gate voltage of the NMOS transistor. By controlling the gate voltage the NMOS transistor generates weighted current just like biology synapse. To test the bidirectional transmission function of the synapse, the neurons works as an oscillating ring, one neuron updates the state of the other neuron based on its own state. The neuron consists of a capacitance and inverters. The capacitance enables the neuron collect information (weighted current) from multiple inputs and the inverter works as an analog amplifier with threshold that determine the state of neuron according to the accumulated charge in the capacitance.

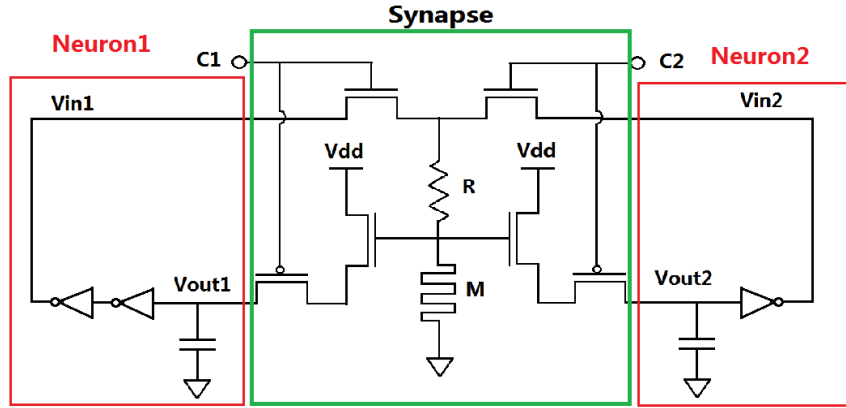


Figure 13, Schematic of Neurons Connected with Memristor-based Bidirectional Synapse

The schematic is simulated in Cadence Virtuoso and result is shown in Figure 14. When the switch signal (C1) is '1', neuron1 updates neuron2's state with neuron1's state. And when C1 is '0', the synapse works in the other way around, neuron2 changes neuron1's state with the opposite state of neuron2. In the beginning of the simulation, the initial states of both neurons are '1', at 30 us capacitance of neuron1 is discharged because Vin2 is '0'. As the data is stored as charge in capacitance, the neuron oscillating ring has very good tolerance of race condition.

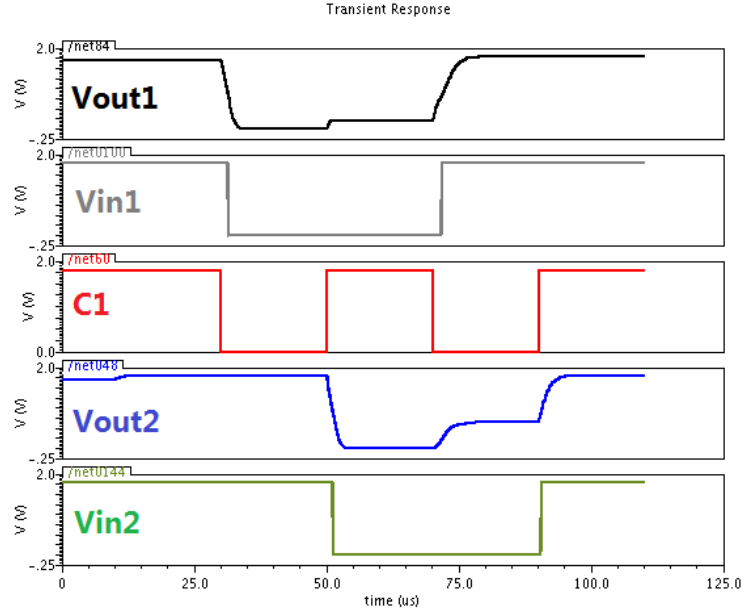


Figure 14, Simulation result of neuron-synapse oscillating ring

An advantage of the neuron-synapse oscillating ring is that the oscillating frequency is determined by the weight of the synapse. With larger memristance, the gate voltage is higher and weighted current is stronger, which means the charging period of the capacitance is longer.

6.2 EXCITATION/INHIBITION TRANSMISSION

In real biology neural system and artificial neural network models, synapse transmits excitation or inhibition between neurons according to different function. There have to be inhibitions in the system because in interconnected networks, excitation begets more excitation. Interneurons, by way of their inhibitory actions, provide the necessary autonomy and independence to neighboring

principal cells. So one of the basic components of neuromorphic computing system is synapse with ability of excitation/inhibition transmission, while previous research on memristor-based synapse design only focus on weighted excitation signal transmission. Figure 15 shows the schematic of synapse we proposed to implement excitation/inhibition transmission. As we use capacitance in previous neuron design, excitation/inhibition could be implemented by charge (pull up)/discharge (pull down) of the capacitance. The truth table of the Excitation/Inhibition synapse is shown in Table 3. Signal '+/-' is to determine whether this synapse will implement a 'Excitation' or 'Inhibition' function of the input signals. When V_{in1}/V_{in2} is '1' and '+/-' is '1', it means the input signal in positive and synapse will transmit it as a excitation, then V_c (XOR output of input signal ' V_{in1}/V_{in2} ' and '+/-') will be '0', which will enable P-transistor and cut off N-transistor to charge the neuron it connects.

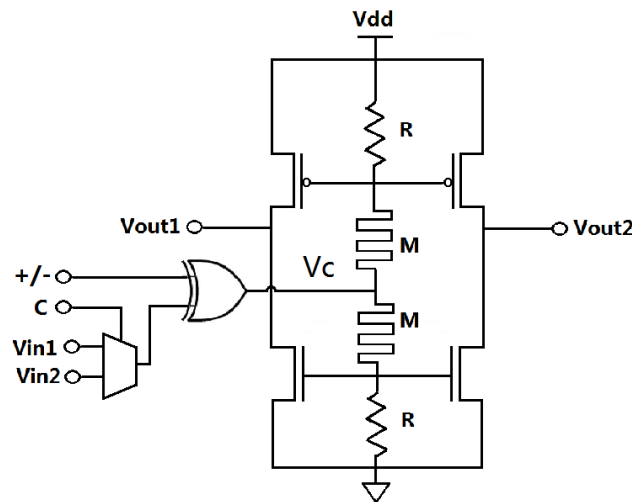


Figure 15, Excitation/Inhibition synapse.

Table 3, Excitation/Inhibition synapse Truth Table

Vin1/Vin2	+/-	P-transistor	N-transistor	Vout1/Vout2
1	1	Pass	Cut off	Pull up
1	0	Cut off	Pass	Pull down
0	1	Cut off	Pass	Pull down
0	0	Pass	Cut off	Pull up

To demonstrate the weighted Excitation/Inhibition transmission ability of the synapse we proposed, a simple information collecting neuron demo (shown in Figure 16) is designed and simulated in Cadence environment.

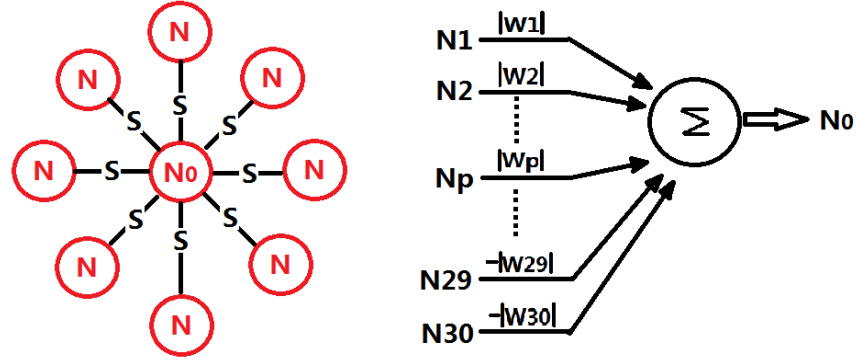


Figure 16, Information Collecting Neuron Demo.

In this demo, neuron N_0 collects information from other neurons through synapses as we proposed. Based on the weighted Excitation/Inhibition signals from 30 other neurons, neuron N_0 makes decision with a non-linear function:

$$N_0 = \begin{cases} 1 & \text{if } \sum_{i=0}^{30} N_i \times W_i \geq \text{threshold} \\ 0 & \text{otherwise} \end{cases} \quad (9)$$

We give different set of excitation weight, inhibition weight to every synapse, and test the state of N0 by increasing the number of positive input neurons. Result is shown as Figure 17.

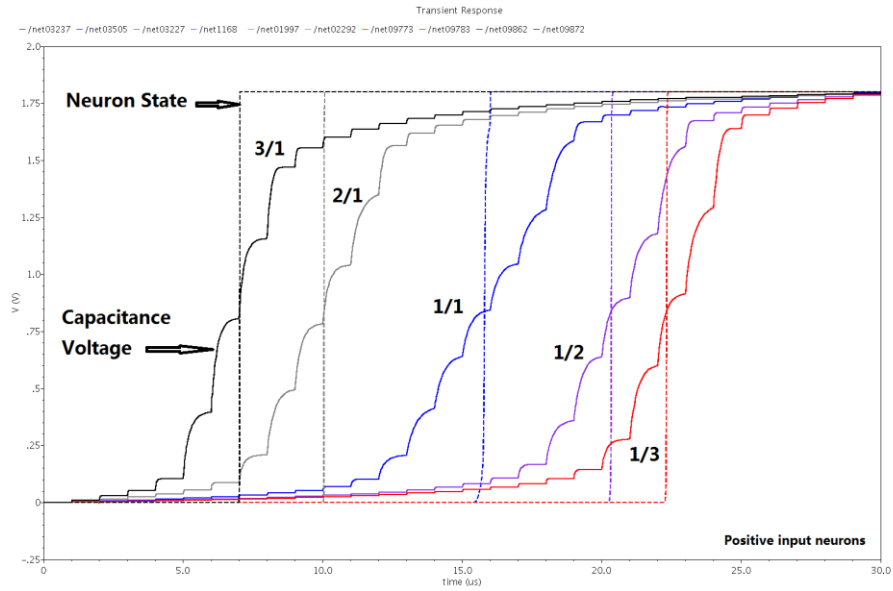


Figure 17, Simulation of Information Collecting Neuron Demo.

Curves from the left to right are test results with positive/negative synapse weights ratio of 3/1, 2/1, 1/1, 1/2, 1/3, and the positive neurons needed to change the state of N0 is 7, 10, 15, 21, 23 accordingly.

6.3 SYNAPSE BASED NEUROMORPHIC COMPUTING SYSTEM

6.3.1 System Architecture

A memristor behaves similarly to a synapse in biological systems and hence can be easily used as the weighted connections in neural networks. Based on the memristor-based bidirectional synapse design, we implement a network serving as neuromorphic computing system with units (artificial neurons) and weighted connections (synapses). The neuron in this network is a binary threshold unit that produces only two different values to represent its state. A synapse works as a weighted connection to transmit a signal from one neuron to another. The activation function can be described in equation (9). The proposed neural network can be used for pattern recognition: first, multiple standard input images are used to train the connection weights of the system till they reach convergence; after that, any input pattern will produce to a local minimum, which is a stable state corresponding to one the stored standard patterns. Such a network system can even be used to recognize the input image with defects. In our experiment, we build a network with 100 (10×10) neurons and store the character images 'A', 'B' and 'C' shown in Figure 18(a) as the standard patterns. Each neuron in the network represents a pixel of the image. Then the defected images in Figure 18(b) are applied as inputs to initialize the network's state. Figure 18(c) show that each input has 13 defects compared to its corresponding standard images (see black bars). The proposed system can completely eliminate the difference to zero and converge to one of the standard patterns, as demonstrated by the write bars in Figure 18(c).

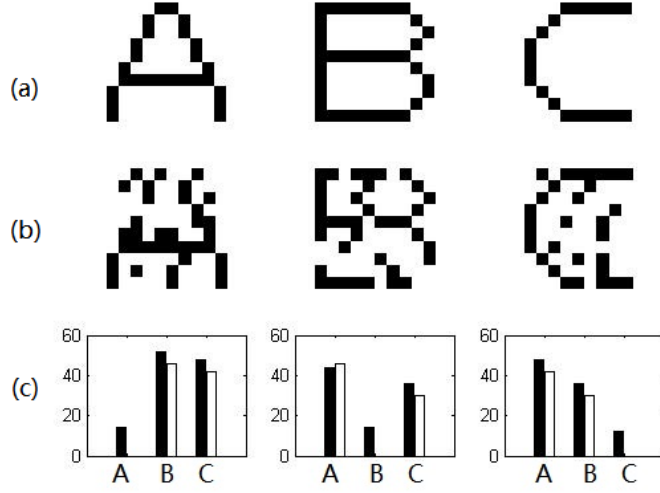


Figure 18, (a) Standard patterns; (b) Noised patterns; (c) Noised input (black bars) VS output.

6.4 SYSTEM EVALUATION

6.4.1 Robustness

The maximal allowed stored standard patterns (capacity) of this neural network design is determined by the amounts of neurons and connections. Moreover, the more patterns stored in the system, the higher precision of the connection weights is needed. Therefore, a large number of stored patterns and the high process variation on memristances will result in a higher failure probability (Pf). To quantitatively evaluate the impact of memristance variations and robustness of the proposed neural network design, we conducted Monte-Carlo simulations for the network with 100 (10×10) neurons. Random variations following Gaussian distribution have been injected to the memristors. And σ is the standard deviation of the memristance. The system could fail to recognize the noised patterns or mismatch an input with other standard patterns due to the

inaccurate connection weights. To test the failure probability under different conditions, we ran 10,000 Monte-Carlo simulations by varying the memristance variation σ when 7, 8, 9, or 10 patterns are stored in the system. In this experiment, each input image contains 21 defects among 100 pixels.

The simulation results in Figure 19 demonstrate that the proposed memristor-based neuromorphic system has a high tolerance on memristance variations. When $\sigma < 0.4$ Pf of all the four configuration are close to the ideal condition at $\sigma = 0$. This indicates that even a large process variation exists in memristor devices; the performance of the proposed neuromorphic system is not affected much. Further increasing $\sigma > 0.5$, Pf grows significantly. As expected, under the same process variation condition, the system suffers a higher Pf when more patterns are stored.

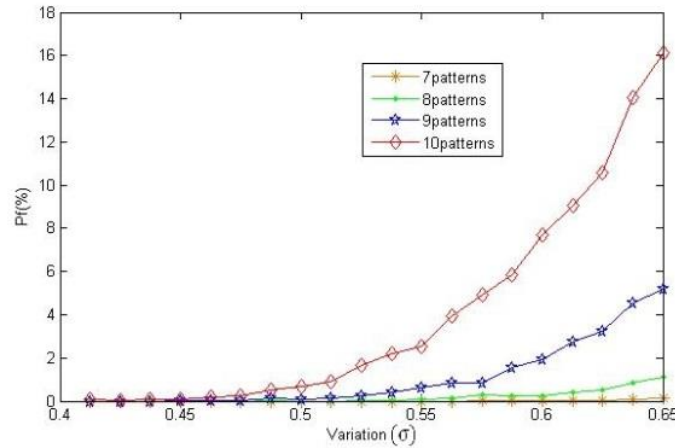


Figure 19, The Impact of Memristor Variations on the Probability of Failure (Pf)

6.4.2 Capacity Analysis

For the artificial neural network we implemented last month, the capacitance works as a key factor to the robustness of the system. It shows that if error in recalling is allowed, the maximum number p of the patterns to be stored in a network with N neurons is $0.15N$ [19]. The limitation is attributed

to the fact that the network is trapped to the so called spurious local minima. In 1987 McEliece et al. [9] proved that when $p < N/4 \ln N$ holds, the Hopfield's model is able to recall all the memorized patterns without error.

For demonstration, we conducted Monte-Carlo simulations to evaluate the impacts of the capacity on the robustness of our networks. A large Hopfield network with 100 neurons is built to recognize larger sets of text patterns where the respective theoretical capacity is limited to about 18 patterns. Process variations are simulated by introducing Gaussian distribution noise to the memristance of the memristor devices in Matlab simulations. A system failure is defined as converging to a wrong standard pattern (ones that do not correspond to the input pattern), or failing to converge to a stable point. The test results are shown in Figure 20. Here σ is the standard deviation of the memristance and Pf is the system failure rate.

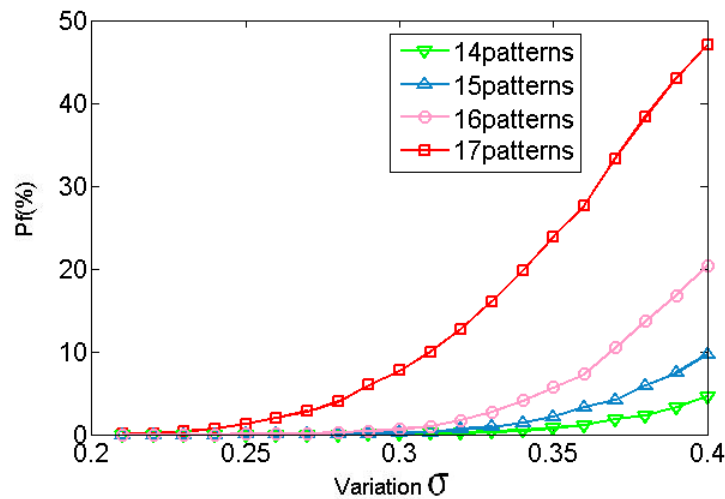


Figure 20, Failure Rate of Hopfield Network under Different Patterns and Process Variation.

Figure 20 shows that our design has a good immunity against process variations: Even when $\sigma < 0.2$, our system still demonstrates a Pf close to zero. Increasing the number of text patterns quickly degrades the system's robustness with much higher Pf values. When the pattern number approaches the capacity limit, the pace of the system robustness degradation rises quickly. Increased process variations (σ) were also shown to degrade system robustness. However, in conventional CMOS circuit manufacturing, the parametric standard deviation is usually less than 10% [16][18].

For the same amount of stored patterns, a larger network with more neurons is more robust to process variations. Figure 21 compares the performance of the systems with 100 neurons (the blue line) and with 400 neurons (the green line). Both systems have 10 standard patterns. And the input defect rate remains at 21% for the two designs. The simulations show that the impact of process variations is smaller and therefore the required precision of connection weights is lower in a bigger network. Hence, in a neural network system design, the tradeoff between network capacity and robustness need to be considered.

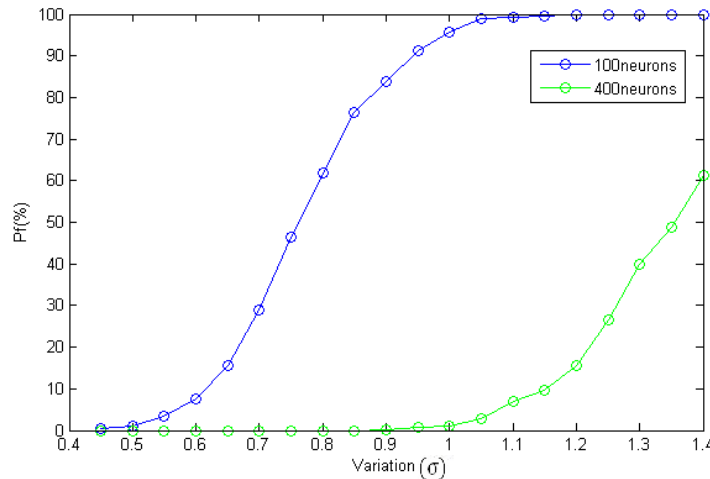


Figure 21, Increasing the Network Size VS Pf.

6.5 COMPARISON BETWEEN CROSSBAR AND SYNAPSE BASED ARCHITECTURE

Figure 22 shows the synapse-based image smoothing processor. Input neurons matrix (red) stores the original image, in which each neuron represents the value of a pixel. Each neuron in output matrix (green) will be calculated by weighted summation of neighbor input neurons:

$$No(i, j) = \frac{1}{4} (Ni(i, j) + Ni(i + 1, j) + Ni(i, j + 1) + Ni(i + 1, j + 1)) \quad (10)$$

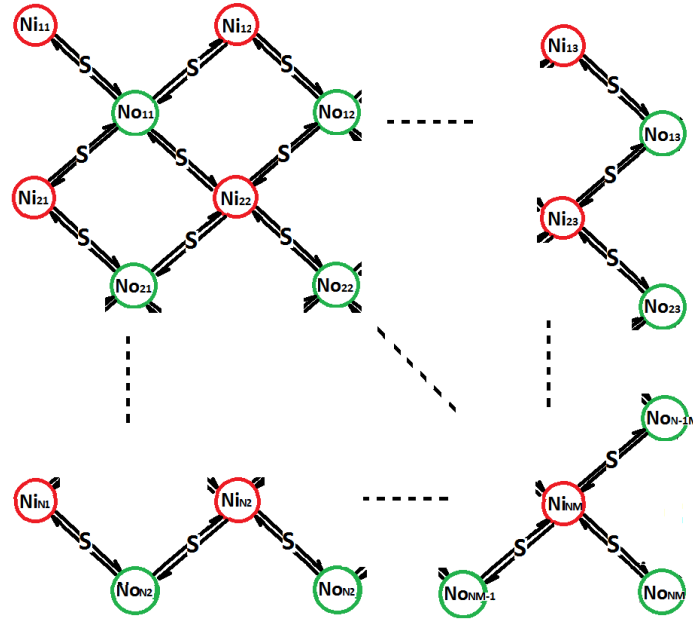


Figure 22, Synapse-based Image Smoothing Processor.

The synapse-based architecture is very efficient for this function because it is local processing, in which there is no connections between long distance neurons. If we implement the same function with crossbar-based architecture, the weighted matrix will be a sparse matrix that only has two non-zero elements in each row or column. But for fully connected network, circuit

area consumption efficiency of these two architectures depends on system capacity. Crossbar has peripheral analog circuit that domains the circuit area when system capacity is small while synapse shows less efficiency for large system. We give a general case estimation in Figure 23, which shows that for system of more than 320 crossbar-based architecture has better efficiency.

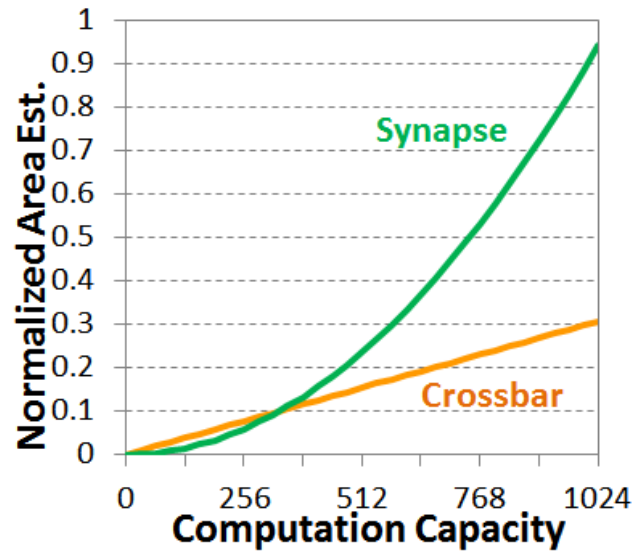


Figure 23, Synapse-based Image Smoothing Processor Area Cost.

7.0 CONCLUSION

In this thesis, we proposed a noise-eliminating training method and digital-assisted initialization step to improve the training process robustness and the performance of memristors crossbar-based neuromorphic computing engine. Experimental results show that our techniques can significantly improve the recall success rate and training time of neuromorphic computing system by up to 18.7%~36.2% and 12.6%~ 14.1%, respectively, through suppressing the noise accumulation in the training iterations and reducing mismatch between the initial weight matrix state and the target value.

We also proposed a memristor-based bidirectional transmission exhibition/inhibition synapse and implemented neuromorphic computing demonstration with our proposed synapse. Experiment results show that the proposed design has high tolerance on process variation and input noise.

In the end, memristor crossbar-based and synapse-based neuromorphic computing architectures are compared and discussed on circuit area consumption efficiency. The synapse-based architecture is very efficient for this function because it is local processing, while crossbar shows high efficiency in fully connected network.

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